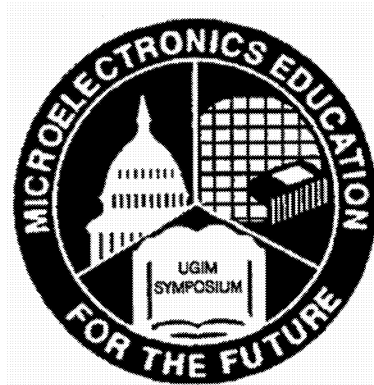


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Session

2.1 Establishing Chip Scale Packaging (CSP) Capabilities at the University of Alaska Fairbanks: Lessons Learned in Tech Transfer, R&D, and Sustaining	Pramod C. Karulkar, David A. Bunzow, Lawrence Bowman, John Hunt, Philip Severs, David Thomas, Jami Warrick, John Dickinson	U. Alaska	1
2.2 Development of a Deep-Submicron CMOS Process for Fabrication of High Performance 0.25 μm Transistors	Michael Aquilino, Dr. Lynn F. Fuller	RIT	7
2.3 RIT MEMS Fabrication Course	Robert E. Pearson, Lynn F. Fuller, Ivan Puchades	RIT	13
2.4 Building the New Berkeley Microfab	A. William Flounders, Katalin Voros	Berkeley	19
2.5 25 Years of Microelectronic Engineering Education	Santosh K. Kurinec, Lynn F. Fuller, Bruce W. Smith, Rickard L. Lane, Karl D. Hirschman, Michael A. Jackson, Robert E. Pearson, Dale E. Ewbank, Sean L. Rommel, Sara Widlund, Joan Tierney, Maria Wiegand, Maureen Arquette, Charles Gruener, Scott P. Blondell	RIT	23
3.1 RF Physical Device Simulation For Wireless Applications	O.L. Hartin, Evan Yu	Freescale	33
3.2 Three-dimensional TCAD Process and Device Simulations	I. Avci, P. Balasingam, K. El Sayed, J. Gharib, M.D. Johnson, K. Kells, G. Kiralyfalvi, V. Koltzyhenkov, A. Kucherov, E. Lyumkis, O. Penzin, B. Polsky, V. Rao, S.D. Simeonov, N. Strecker, Z. Tan, L. Villablanca, W. Fichtner	Synopsys	41
3.3 Investigation of the Performance limits of III-V Double-Gate n-MOSFETs	Abhijit Pethe, Tejas Krishnamohan, Donghyun Kim, Saeroonter Oh, H.S. Philip Wong, Krishna Saraswat	Stanford	47
3.4 Simulation of Quasi-stationary and Transient Effects in GaN Based Heterostructure Field Effect Transistors	N. Braga, R. Mickevicius, V. Rao, W. Fichtner	Synopsys	51
3.5 A 2-Mask NMOS Process Design Fabricate and Test Module for Use in Microelectronics Instruction and Process Development	D.W. Parent	SJSU	57
4.1 Effect of Process and Layout on Strain Enhancement from Dual Stress Liners	Victor Moroz, Munkang Choi, Xi Wie Lin, Dipu Pramanik	Synopsys	63
4.2 Modeling Process Impact on Cu/Low k Interconnect Performance and Reliability	Xiaopeng Xu, Greg Rollins, Xiao Lin, Dipu Pramanik	Synopsys	65
4.3 Lithography Challenges toward Nano Scaled Device	HeeMok Lee, JinSoo Kim, YoungKeun Cho, SangCheol Jeon, KiNam Kim, KwangHee Kim, JaeSub Oh, HeeChurl Lee	NNFC	71
5.1 Academic Development in Test Engineering	Tamara A. Papalias, R. Bryan Gonzales, Frank Gurtovoy	SJSU	77
5.2 Low Budget Undergraduate Microelectronics Laboratory	David J. Hunt	Alfred State	81
5.3 Survey of University Micro/Nanotechnology Cleanroom Facilities as the First Phase in the Development of a U of L Business Model	Kevin Walsh, Mark Crain, Robert Keynton, Lisa Itamura, Scott Smith, Bruce Kemelgor	U. Louisville	89
5.4 National NanoFab Center (NNFC): Nanofabrication Facility	Jong Wan Park, Jeoung Woo Kim	NNFC	97
5.5 A University-Technical College Nanoscience Training Program	Greg Cibuzar, Steve Campbell, Greg Haugstad, Michael Flickinger, Deb Newberry, Karen Halverson, Micheal Opp	U. Minnesota / DCTC	101

Session

6.1 Low-Noise Amplifier Circuit for Embedded Electrophysiological Recording with Adjustable Gain and High-Pass Filtering	Shahin Farshchi, Jack W. Judy	UCLA	105
6.2 Si-based Resonant Interband Tunnel Diode/CMOS Integrated Memory Circuit	Stephen Sudirgo, David J. Pawlik, Karl D. Hirschman, Sean L. Rommel, Santosh K. Kurinec, Phillip E. Thompson, Paul R. Berger	RIT / NRL / Ohio State	109
6.3 Numerical and Analytical Results for the Polysilicon Gate Depletion Effect on the MOS Gate Capacitance	H. Abebe, E. Cumberbatch, H. Morris, V. Tyree	USC / MOSIS	113
6.4 Compact Models for I-V Characteristics of Double Gate and Surround Gate MOSFETs	H. Abebe, E. Cumberbatch, H. Morris, V. Tyree	USC / MOSIS	119
6.5 Evaluation of a Double Implanted Diffused MOSFET for Analog Operation	Eric J. Basham, David W. Parent	SJSU	125
7.1 Large Stroke Actuators for Adaptive Optics	Bautista Fernández, Joel A. Kubby	UCSC	131
7.2 Experimental Studies on the Effects of Geometric Parameters in a Planar Pneumatic Microvalve	K.J. Maung, J. Chan, S.J. Lee	SJSU	137
7.3 Advanced Studies into the Hermeticity of Micro-Electronic and Micro-Ordnance Devices	Karl K. Rink, George R. Neff, Jimmie K. Neff	U. Idaho / Iso Vac Eng.	143
7.4 Low Cost, Tailored Polymer-Metal Nanocomposites for Advanced Electronic Applications	Abhijit Biswas, Pramod C. Karulkar	U. Alaska	145
7.5 Wuhan National Laboratory for Optoelectronics and Its Collaboration with Georgia Tech	Zhiping Zhou	Georgia Tech	151
8.1 V_T Adjustment by L_{eff} Engineering for LSTP Single Gate Work-function CMOS FinFET Technology	Vidya Varadarajan, Tsu-Jae King Liu	Berkeley	155
8.2 Impact of Millisecond Anneals on CMOS Scaling - A Device Simulation Study	Sunderraj Thirupapuliur	Applied Materials	159
8.3 Low Temperature Dopant Activation for Integrated Electronics Applications	Eric M. Woodard, Robert G. Manley, Germain Fenger, Robert L. Saxer, Karl D. Hirschman, David Dawson-Elli, J. Greg Couillard	RIT / Corning	161
9.1 Modeling and Analysis of the Charging Dynamics in Si-quantum Dots Based Non Volatile Flash Memory Cells	Pavan Singaraju, Rama Venkat, Samar Saha	UNLV / Synopsys	169
9.2 Signal Enhancement of Time-resolved Magneto-optic Measurements on Individual Nanomagnets	Suqin Wang, Naser Qureshi, Mark A. Lowther, Aaron R. Hawkins, Sunghoon Kwon, Alexander Liddle, Jeffrey Bokor, Holger Schmidt	UCSC	175
9.3 Integrated ARROW Waveguides for Molecule Specific Surface-enhanced Raman Sensing	Philip Measor, Leo Seballos, Dongliang Yin, John P. Barber, Aaron R. Hawkins, Jin Zhang, Holger Schmidt	UCSC	181
9.4 Phonon Confinement in Germanium Nanowires	Xi Wang, Ali Shakouri, Bin Yu, Xuhui Sun, Meyya Meyyappan	UCSC / NASA	183
9.5 The Design of MOS-BJT-NDR-Based Cellular Neural Network	Dong-Shong Liang, Yaw-Hwang Chen, Chun-Min Wen, Chun-Da Tu, Kwang-Jow Gan, Chershiung Tsai	Kun Shan U.	189

Session

10.1 Leakage Current in DRAM Memory Cells	Jonathan Yu, Koorosh Aflatooni	SJSU	191
10.2 A Gain Control Low Power CMOS Power Amplifier for Ultra Wideband Applications	Jack C. Reed, Houshang Amir Aghahassan, Jane Chi, Albert Yen	UMC	195
10.3 A 2.4-GHz, Wide Tuning Range GmC VCO Using a Novel Load Biasing Technique	Vivek Verma, Tamara Papalias	SJSU	201
10.4 Lithography Solutions for a .35 μ m 25V PDMOS Technology	Brett Williams, Mike Thomason, Chuck Belisle, Bruce Greenwood	AMI Semiconductor	207
10.5 Advanced Process Simulation - Laser and Flash Annealing	Mark E. Law	U. Florida	213
11.1 6 Bit Decimation Filter in Sub-threshold Region	Ritu Jain, Pratibha Guttal, D.W. Parent	SJSU	215
11.2 Frequency Multiplier Design Based on Multiple-Peak R-BJT-NDR Devices Fabricated by SiGe Technology	Dong-Shong Liang, Kwang-Jow Gan, Chun-Da Tu, Cher-Shiung Tsai, and Yaw-Hwang Chen	Kun Shan U.	221
11.3 Studying the Etch Rates and Selectivity of SiO ₂ and Al in BHF Solutions	Meow Yen Sim, Stacy Gleixner	SJSU	225
11.4 Implementation of On-line Error Detecting, Constant Delay, Carry Free Adder	Yugandhar Asmath	SJSU	229
11.5 Pixel Level Analog to Digital Converter	Nguyen Phong, Chung Joseph, Mariavanessa Pascua, Scott Tarkul, Eric Vasham, David Parent	SJSU	233
11.6 Improvement of a 4-mask Process Recipe	Kuang-Wai Tseng, Mariavanessa Pascua, Taslima Rahman, Siu Kuen Leung, Scott Echols	SJSU	237
11.7 Design of an Ultra-Low Power Receiver for 2.4GHz Applications in 90nm CMOS	Maryam Tabesh, Koorosh Aflatooni	SJSU	241